

碳化矽 SiC 單晶片參數表

Parameters of Semi-insulating SiC Single Crystal Wafer

Diameter	2" ; 3"
Polytype	6H
Resistivity	$> 10^5 \Omega\text{cm}$
Micropipes	$< 50 /\text{cm}^2$
Thickness	$350 \text{ um} \pm 50 \text{ um}$
Surface Finish	Si side
TTV	$< 40 \text{ um}$
Warp	$< 25 \text{ um}$
Surface coarseness	$< 0.5 \text{ um}$
Usable area	$> 80\%$

- Other orientation, thickness, or other parameters available upon request.